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Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	Not Yet Assigned
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				First Named Inventor	Li Li
				Art Unit	Not Yet Assigned 2823
				Examiner Name	Not Yet Assigned J. PHAM
Sheet	1	of	11	Attorney Docket Number	M4065.0909/P909-A

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		Examiner Name	Not Yet Assigned T. P. HAM
		Attorney Docket Number	M4065.0909/P909-A
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